

**Features:**

- High speed switching
- Voltage drive
- Low inductance module structure

**Typical Applications:**

- Inverter for Motor Drive
- Inverter welding machines
- Uninterruptible Power Supply
- Industrial machines

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VALUE			UNIT
			Min	Type	Max	
$V_{CES}$	Collector-Emitter voltage	$T_J=25^{\circ}\text{C}$			1250	V
$V_{GES}$	Gate-Emitter voltage	$T_J=25^{\circ}\text{C}$			$\pm 30$	V
$I_C$	Collector current	Continuous@ $T_C = 100^{\circ}\text{C}$			100	A
$I_{CP}$		$t_p=1\text{ms}$			200	A
$P_C$	Collector power dissipation	$T_J=150^{\circ}\text{C}$ , 1 device			500	W
$T_J$	Junction temperature	/			175	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature	/	-40		125	$^{\circ}\text{C}$
$V_{iso}$	Isolation between terminal and copper base	$T_J=25^{\circ}\text{C}$ , AC: 1minute	2500			V
Screw torque	Mounting(M6)	/	4.5		6.0	N·m
	Terminals(M5)	/	2.5		4.5	N·m
$I_{CES}$	Zero gate voltage collector current	$T_J=25^{\circ}\text{C}$ , $V_{CE}=1200\text{V}$ , $V_{GE}=0\text{V}$			1	mA
$I_{GES}$	Gate-Emitter leakage current	$T_J=25^{\circ}\text{C}$ , $V_{CE}=0\text{V}$ , $V_{GE}=\pm 20\text{V}$			$\pm 2$	$\mu\text{A}$
$V_{GE(th)}$	Gate-Emitter threshold voltage	$T_J=25^{\circ}\text{C}$ , $V_{CE}=20\text{V}$ , $I_C=100\text{mA}$	5		8.5	V
$V_{CE(sat)}$	Collector-Emitter saturation voltage	$T_J=25^{\circ}\text{C}$ , $V_{GE}=15\text{V}$ , $I_C=100\text{A}$		1.75	2.40	V
		$T_J=125^{\circ}\text{C}$ , $V_{GE}=15\text{V}$ , $I_C=100\text{A}$		1.95		V
		$T_J=150^{\circ}\text{C}$ , $V_{GE}=15\text{V}$ , $I_C=100\text{A}$		2.05		V
$C_{ies}$	Input capacitance	$T_J=25^{\circ}\text{C}$ , $V_{CE}=10\text{V}$ , $V_{GE}=0\text{V}$ , $f=1\text{MHz}$		9.1		nF
$t_{on}$	Turn-on time	$T_J=150^{\circ}\text{C}$ , $V_{CC}=600\text{V}$ , $I_C=100\text{A}$ , $V_{GE}=\pm 15\text{V}$ , $R_G=10\Omega$ , Inductive load		160		ns
$t_r$				40		ns
$t_{off}$	Turn-off time			600		ns
$t_f$				200		ns
tsc	Short Circuit Withstand Time	$T_J=150^{\circ}\text{C}$ , $V_{CC}=720\text{V}$ , $V_{GE}=\pm 15\text{V}$ , $R_G=10\Omega$	10			$\mu\text{s}$
$V_F$	Forward on voltage	$T_J=25^{\circ}\text{C}$ , $I_F=100\text{A}$		1.80	2.6	V
		$T_J=125^{\circ}\text{C}$ , $I_F=100\text{A}$		1.88		V
		$T_J=150^{\circ}\text{C}$ , $I_F=100\text{A}$		1.95		V
$t_{rr}$	Reverse recovery time	$T_J=125^{\circ}\text{C}$ , $I_F=100\text{A}$		135		ns
		$T_J=150^{\circ}\text{C}$ , $I_F=100\text{A}$		150		ns
$R_{th(j-c)}$	Thermal resistance(per chip)	IGBT			0.30	$^{\circ}\text{C/W}$
		FWD			0.50	$^{\circ}\text{C/W}$
$R_{th(c-f)}$	Contact thermal resistance (per module)	With thermal compound		0.05		$^{\circ}\text{C/W}$
$W_t$	Weight				155	g
Outline	251H3					

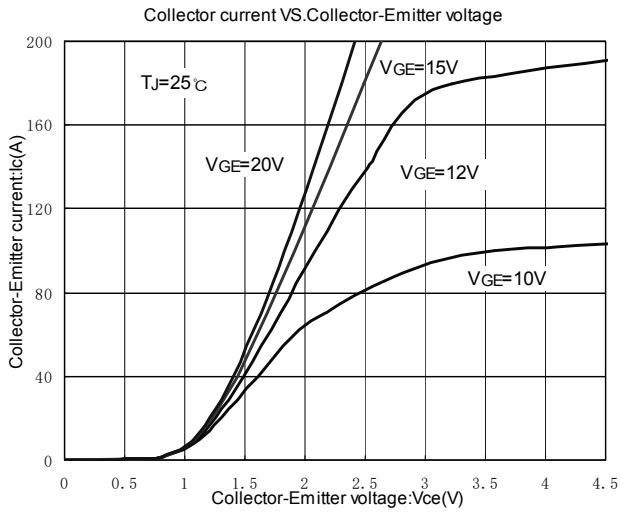


Fig.1

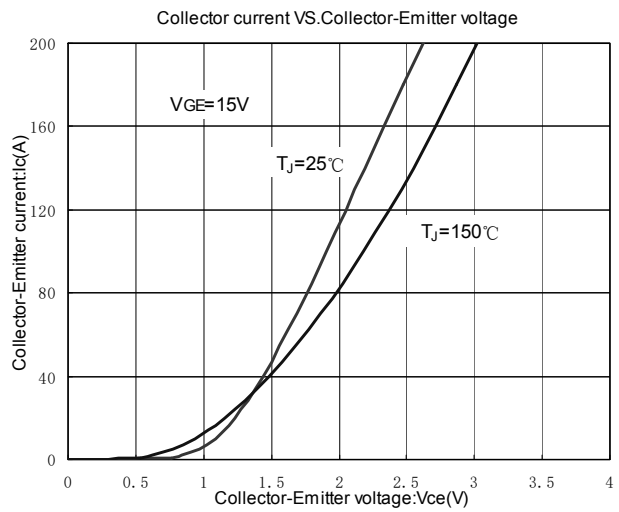


Fig.2

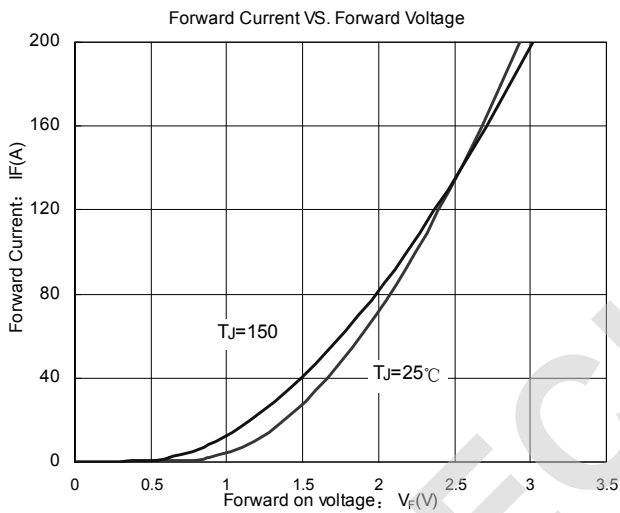


Fig.3

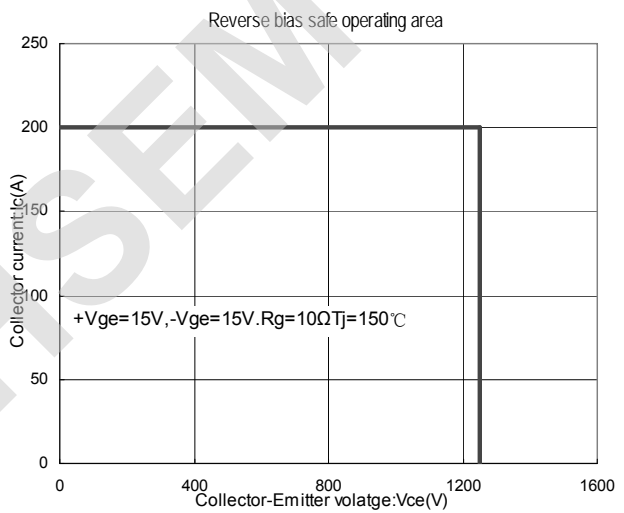


Fig.4

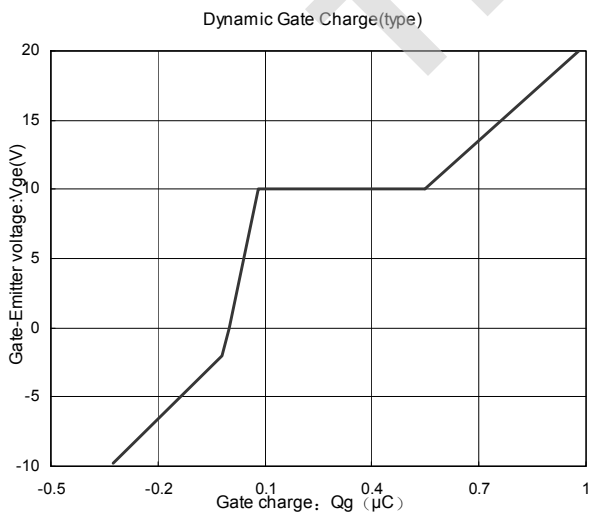


Fig.5

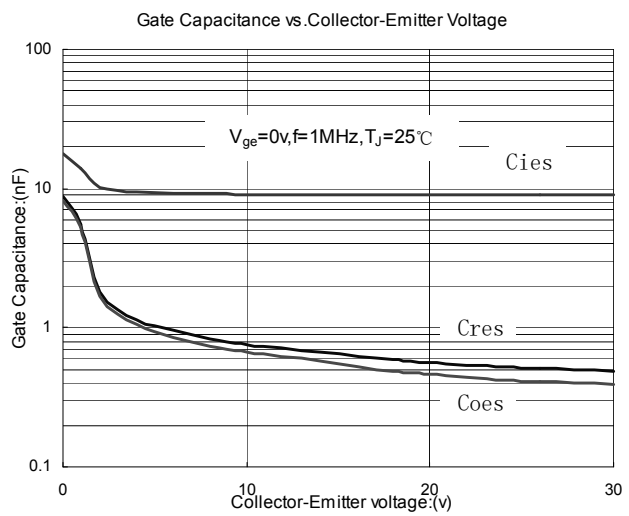


Fig.6

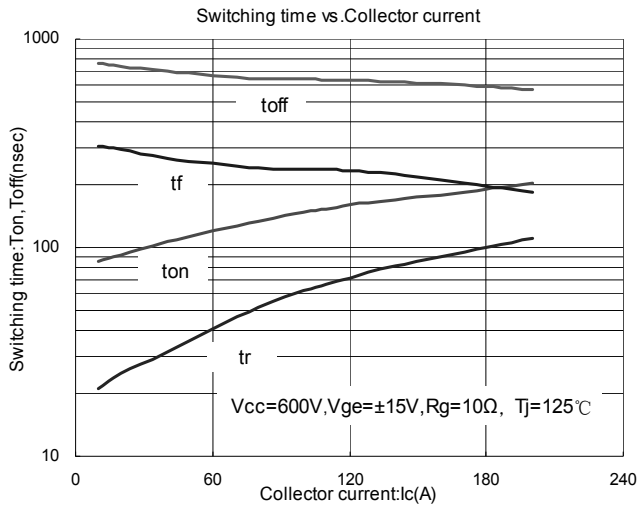


Fig.7

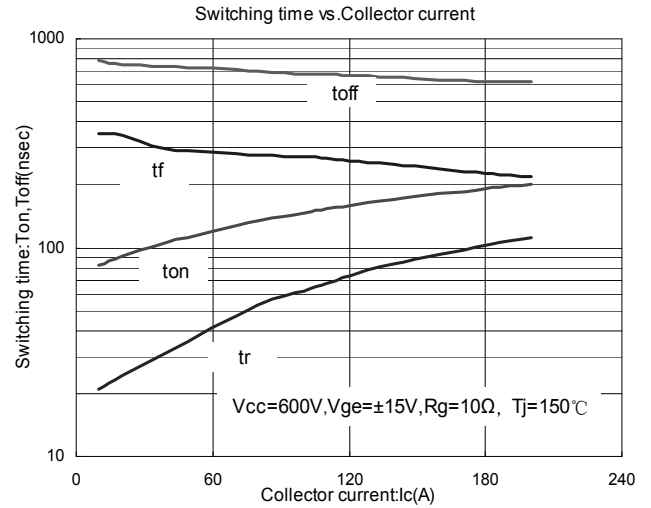


Fig.8

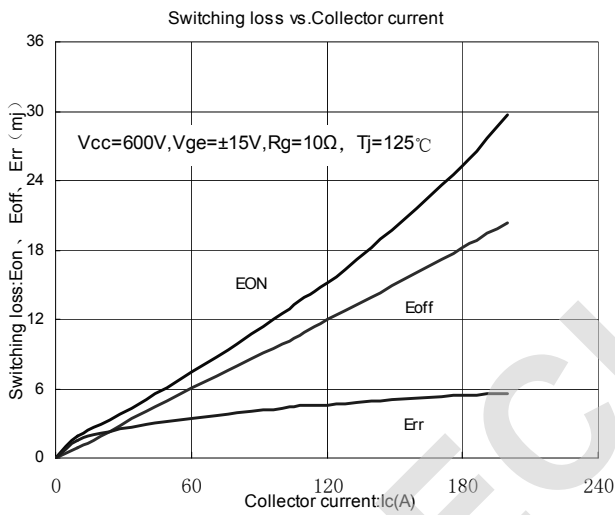


Fig.9

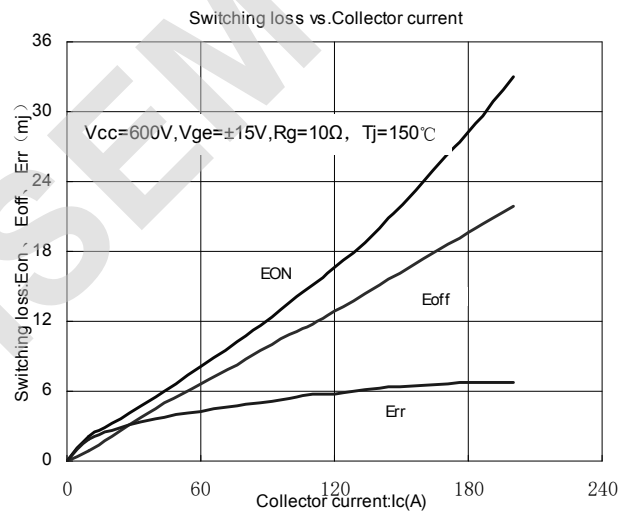


Fig.10

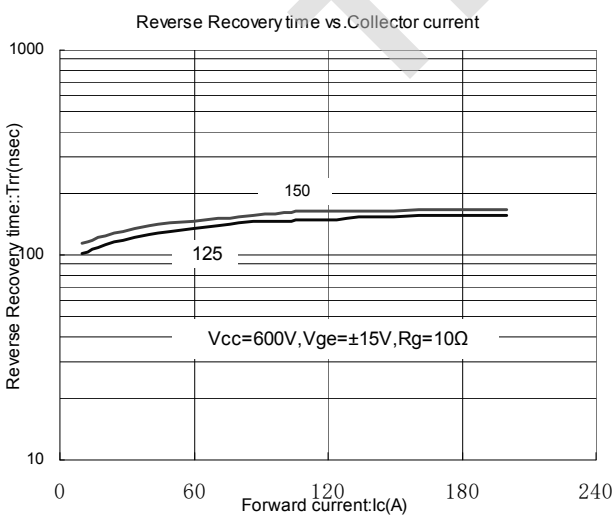


Fig.11

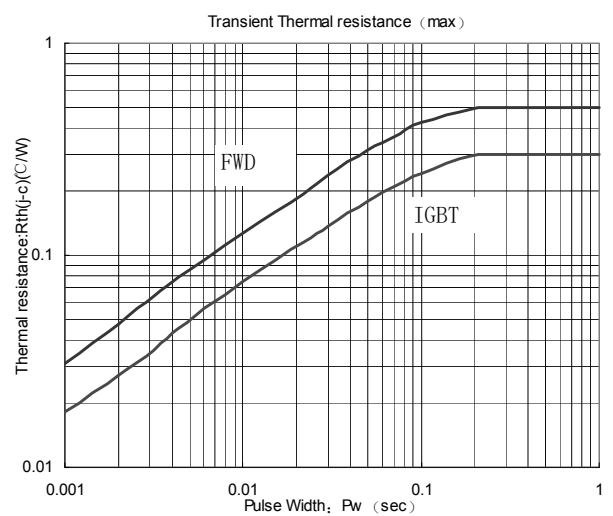
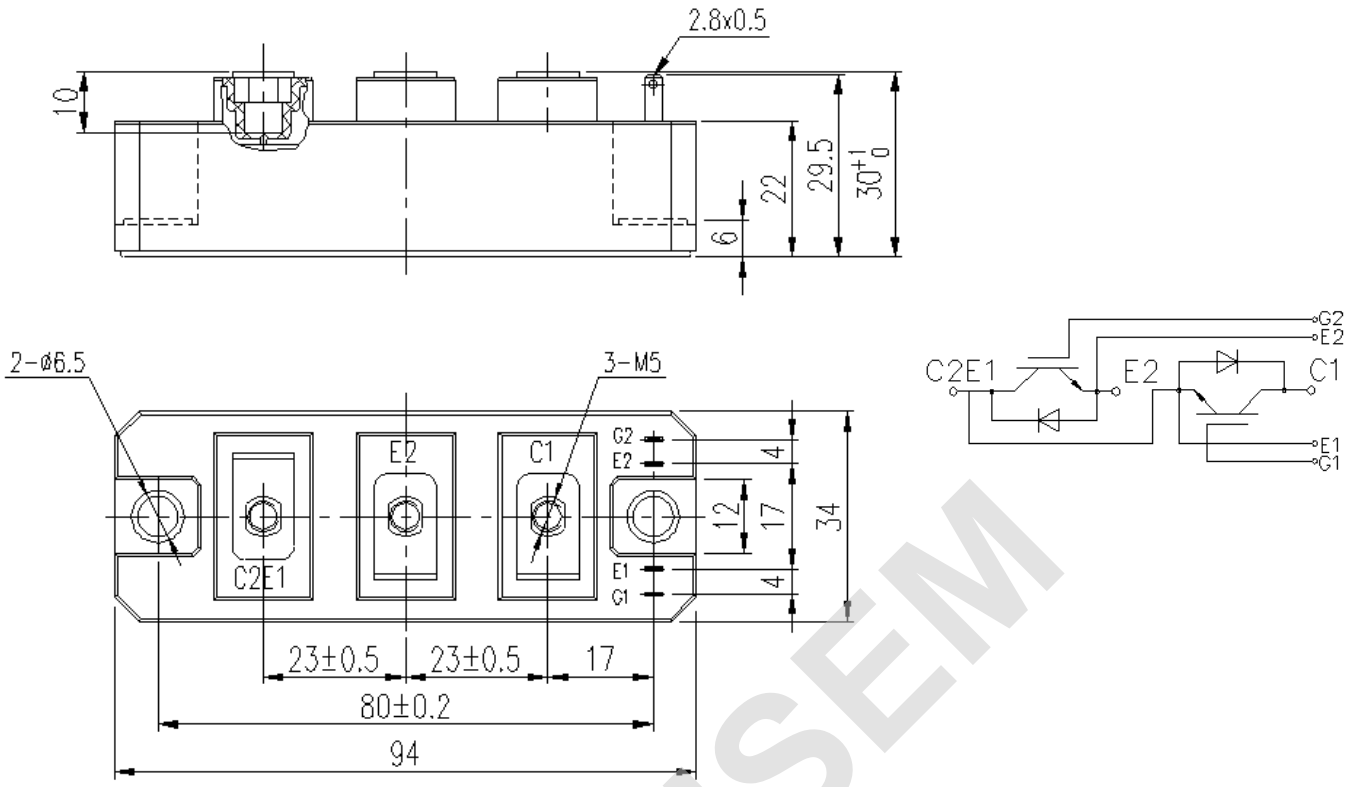


Fig.12

Outline & Circuit Diagram



Unmarked dimensional tolerance: ±0.5mm

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